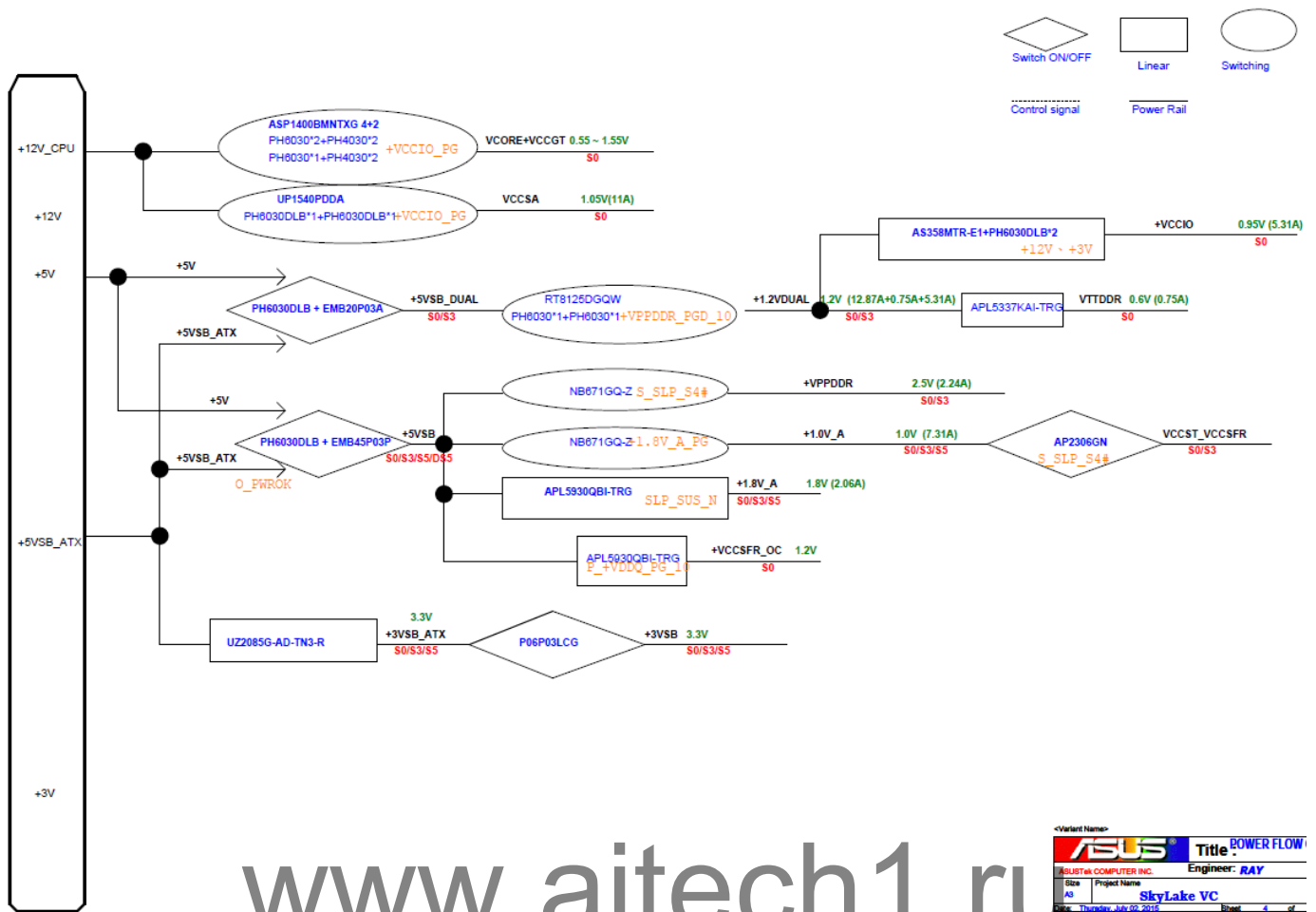


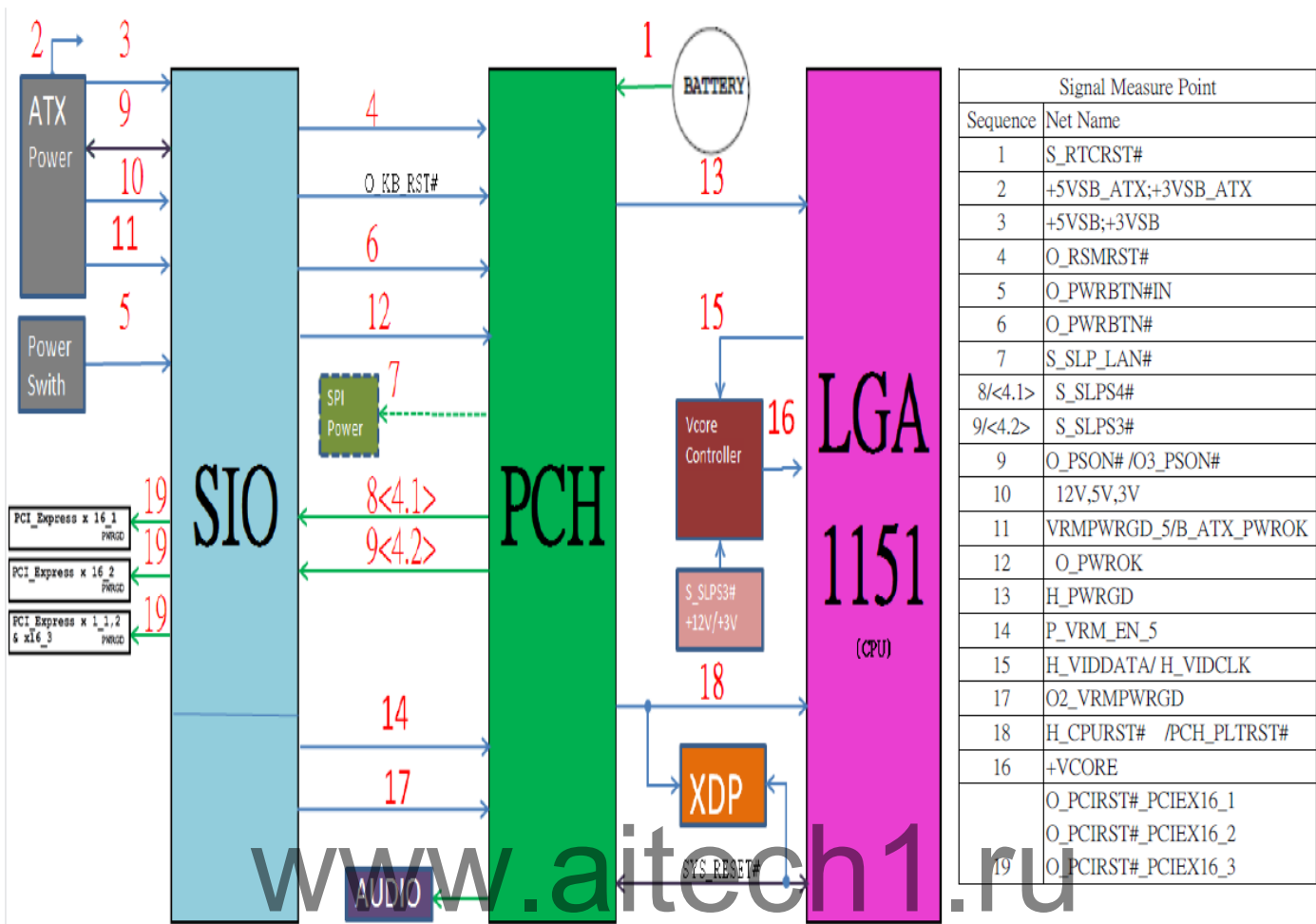
2. POWER FLOW



www.aitech1.ru

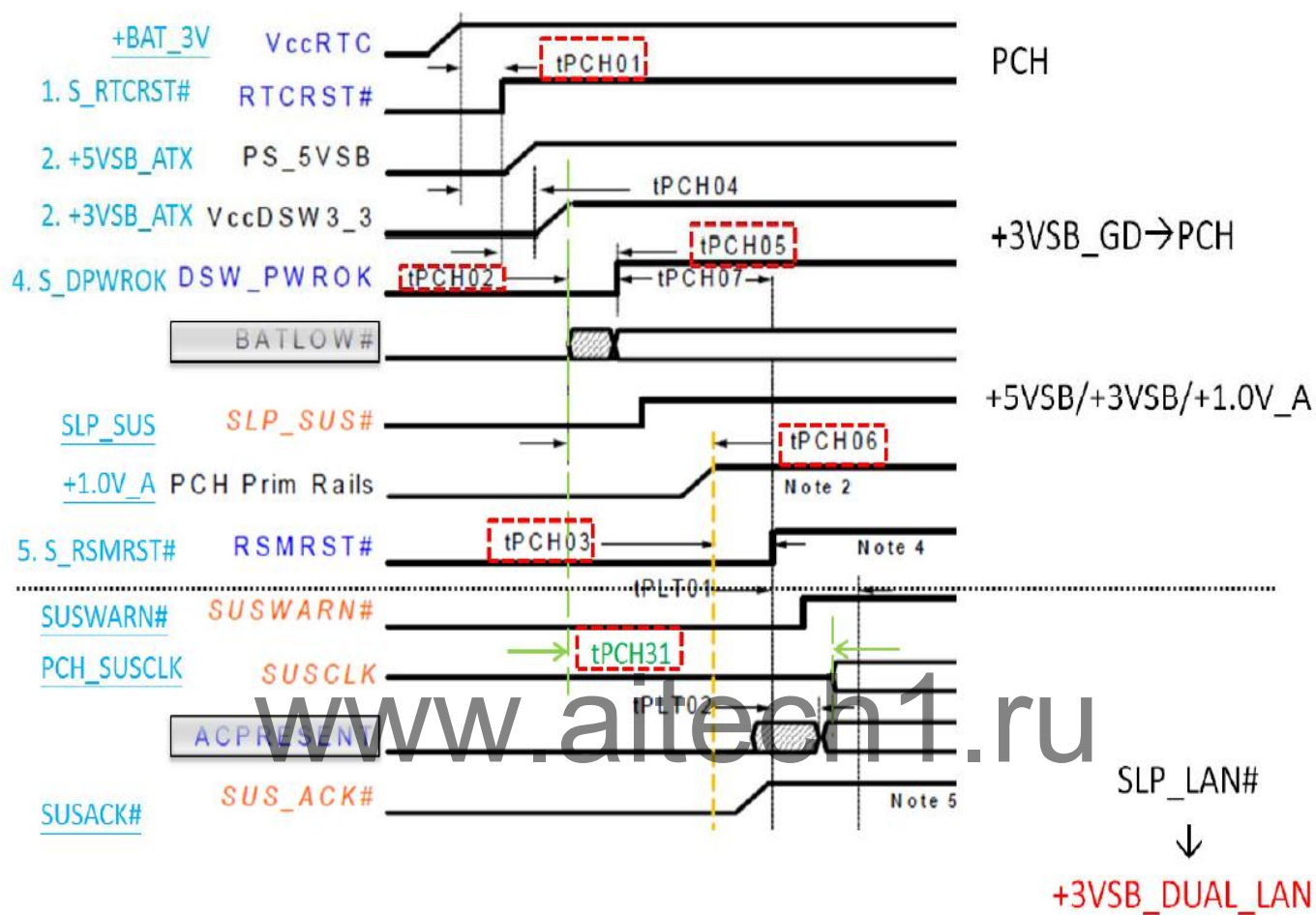
ASUS		Title: POWER FLOW
ROUSTON COMPUTER INC.		Engineer: RAY
Site: AS	Project Name: SkyLake VC	
Date: Thursday, July 02, 2016		Sheet: 4 of 4

3. POWER ON SEQUENCE

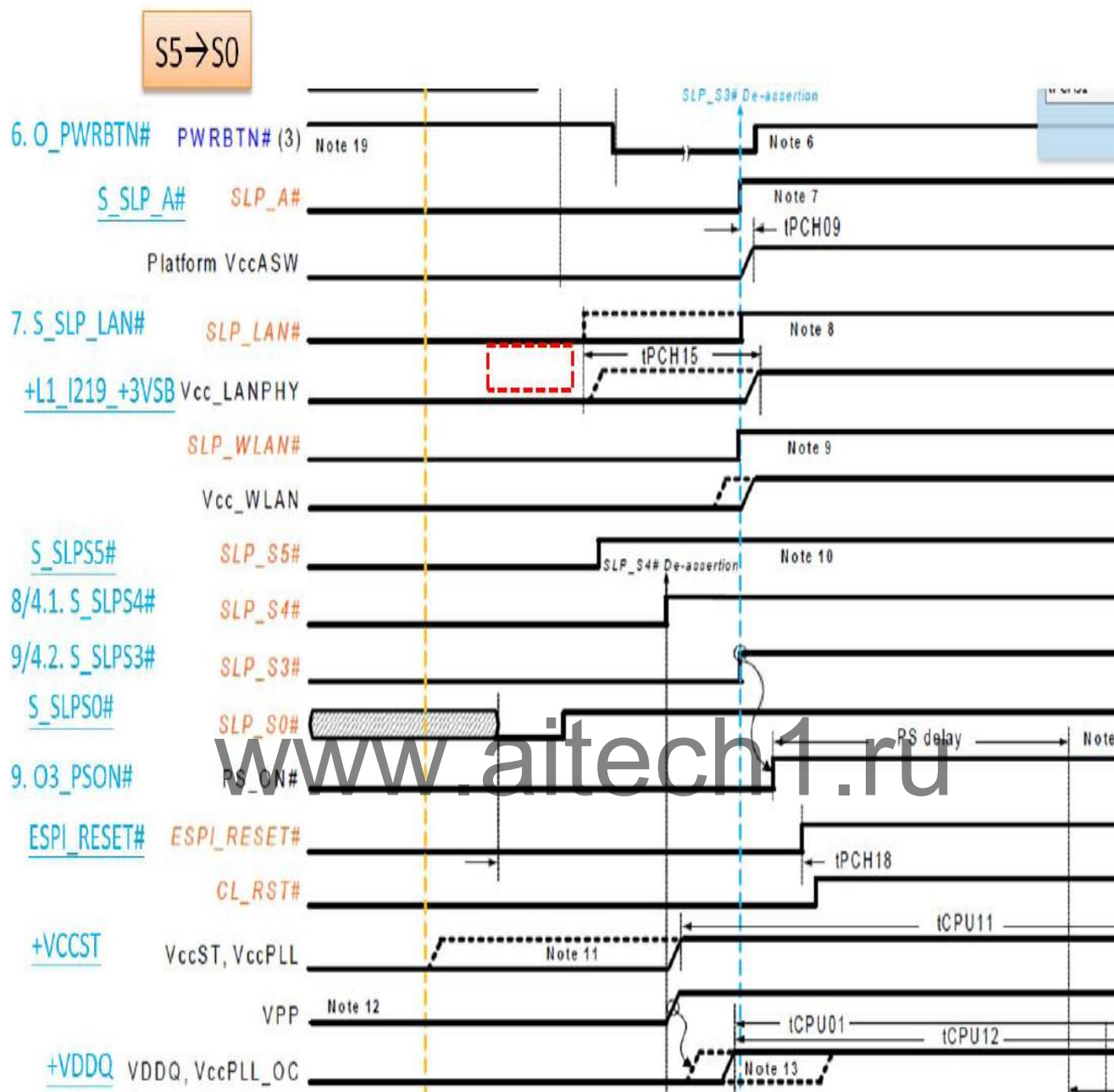


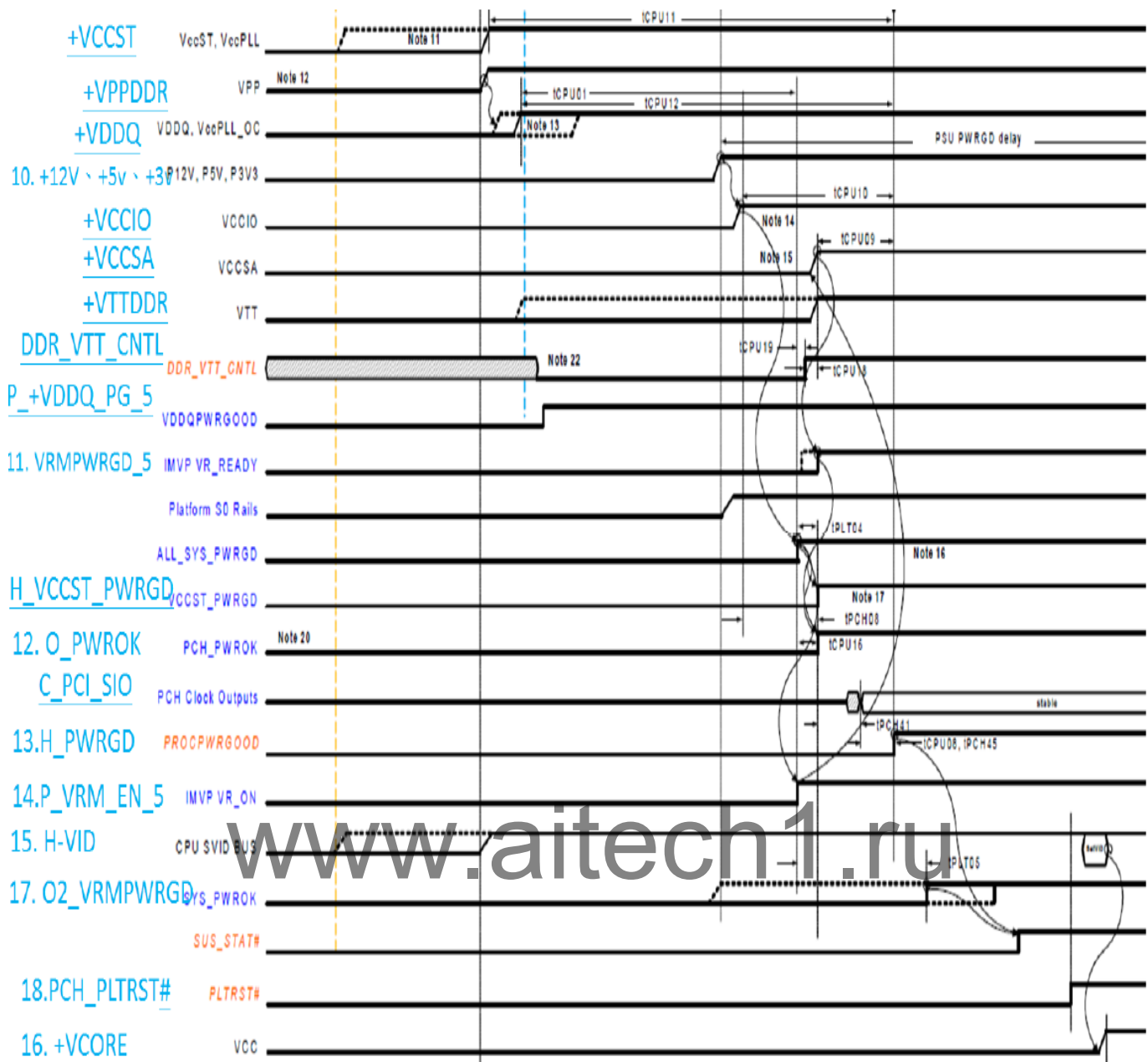
4. Timing Diagram for G3 to S5

G3→S5

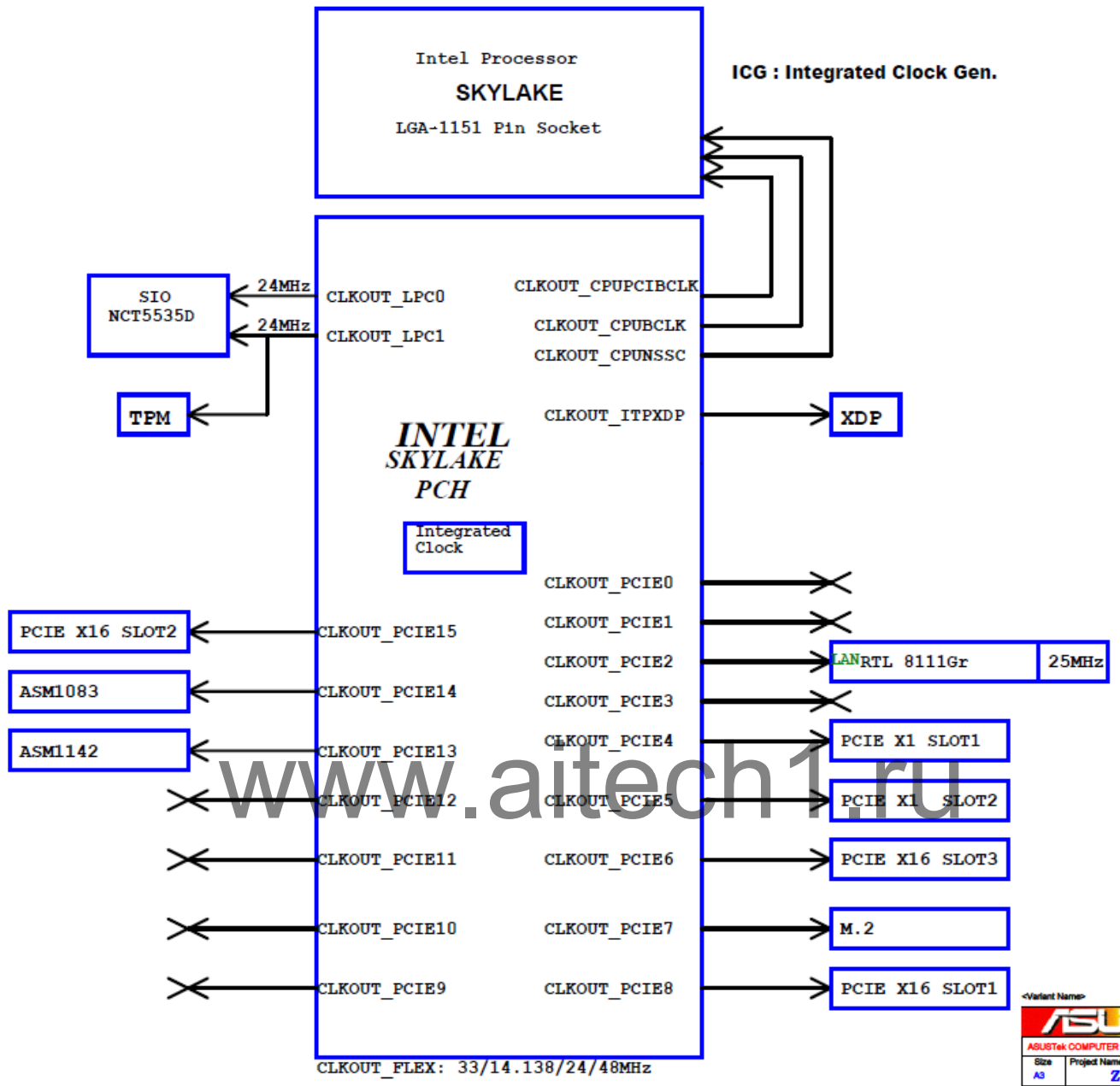


Timing Diagram for S5 to S0/M0





5. Frequency Flow



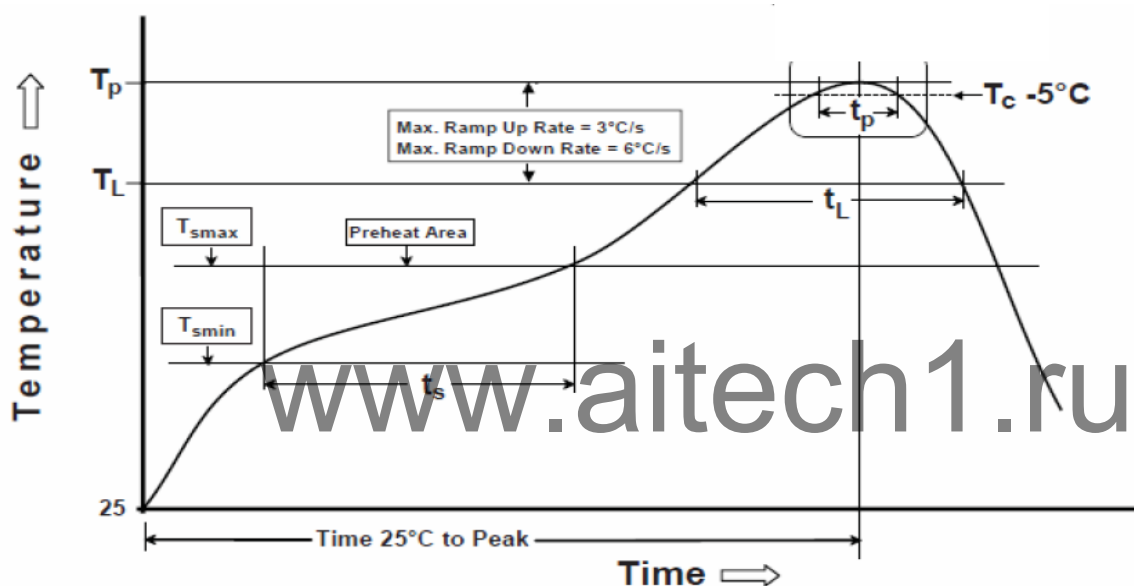
6. Socket reflow profile

Profile Feature	SMD Pb-Free Assembly	DIP Pb-Free Assembly	SMT Component Vendor Spec	DIP Component Vendor Spec
Preheat/Soak				
Temperature Min (T _{min})	150 °C	80 °C	150 °C	135 °C
Temperature Max (T _{max})	200 °C	135 °C	200 °C	need endure 80 seconds
Time (t _s) from (T _{min} to T _{max})	120 seconds	120 seconds	need endure 120 seconds	
Ramp-up rate (TL to Tp)	3 °C/second max.	3 °C/second max.	need endure 3 °C/second max.	need endure 3 °C/second max.
Liquidous temperature (TL)	217 °C	NA	217 °C	NA
Time (t _L) maintained above TL	90 seconds		need endure 90 seconds	
Peak package body temperature (Tp)	260 °C	270 °C	260 °C	270 °C
Time (t _p)* within 5 °C of the specified classification temperature (T _c), see Figure 1-1.	10* seconds	6* seconds	need endure 10* seconds	need endure 6* seconds
Ramp-down rate (Tp to TL)	6 °C/second max.	6 °C/second max.	need endure 6 °C/second max.	need endure 6 °C/second max.
Time 25 °C to peak temperature	8 minutes max.	8 minutes max.	8 minutes max.	8 minutes max.

Note 1: All temperatures refer to the center of the package, measured on the package body surface that is facing up during assembly reflow (e.g., live-bug). If parts are reflowed in other than the normal live-bug assembly reflow orientation (i.e., dead-bug), T_p shall be within ± 2 °C of the live-bug T_p and still meet the T_c requirements, otherwise, the profile shall be adjusted to achieve the latter. To accurately measure actual peak package body temperatures refer to JEP140 for recommended thermocouple use.

2. DIP Plastic heat resistance capability :

- (1) Direct contact 270°C, 6 seconds
- (2) In-direct contact 230°C, 5 seconds
- (3) no contact 130°C, 5 seconds



7. Lead-Free Rework Thermo profile Graphic for BGA & Chipset



Except for body temp, all temperatures are measured with thermo couples inside solder joints, for better accuracy

Primary Factors for Successful Rework:

- Flux formulation and solder paste formulation and volume
- A capable thermal reflow profile
- Proper PCB pad solder preparation/wicking (clean-up of the residual solder

from the PCB pads)

Caution: Always remove batteries and thermal solutions following the system design disassembly process steps prior to BGA rework to avoid damaging the BGA.

View this Intel® BGA / Socket Rework Video (10 minutes in length):

<http://link.brightcove.com/services/player/bcpid1409165005001?bckey=AQ~~,AAAQwZd9wk~,X1Exj3sUi-03b71FGkEmVWbi4T4yGcor&bctid=1519232885001>

8. MB Baking Time: 120 °C, 8 hours

BGA Baking Time:

5.2 Floor Life The floor life of SMDs per Table 5-1 will be modified by environmental conditions other than 30 °C/60% RH. Refer to Clause 7 to determine maximum allowable time before rebake would be necessary. If partial lots are used, the remaining SMD packages must be resealed or placed in safe storage within one hour of bag opening (see 5.3). If one hour exposure is exceeded, refer to 4.1.

Table 5-1 Moisture Classification Level and Floor Life per J-STD-020

Level	Floor Life (out of bag) at factory ambient ± 30 °C/60% RH or as stated
1	Unlimited at ± 30 °C/85% RH
2	1 year
2a	4 weeks
3	168 hours
4	72 hours
5	48 hours
5a	24 hours
6	Mandatory bake before use. After bake, must be reflowed within the time limit specified on the label

Supplier Bake: Default Baking Times Used Prior to Dry-Pack that were Exposed to Conditions ± 60 % RH (“MET” = 24 h)

Package Body Thickness	Level	Bake @ 125° C +10/-0 ° C	Bake @ 150° C +10/-0 ° C
≤ 1.4 mm	2	7 hours	3 hours
	2a	8 hours	4 hours
	3	16 hours	8 hours
	4	21 hours	10 hours
	5	24 hours	12 hours
	5a	28 hours	14 hours
> 1.4 mm ≤ 2.0 mm	2	18 hours	9 hours
	2a	23 hours	11 hours
	3	43 hours	21 hours
	4	48 hours	24 hours
	5	48 hours	24 hours
> 2.0 mm ≤ 4.5 mm	5a	48 hours	24 hours
	2	48 hours	24 hours
	2a	48 hours	24 hours
	3	48 hours	24 hours
	4	48 hours	24 hours
> 4.5 mm	5	48 hours	24 hours
	5a	48 hours	24 hours

Note 1: If baking of packages > 4.5 mm thick is required see appendix B.

Note 2: The bake times specified are conservative for packages without blocking planes or stacked die. For a stacked die or BGA package with internal planes that impede moisture diffusion the actual bake time may be longer than that required in Table 4-2 if packages have had extended exposure to factory ambient before bake. Also the actual bake time may be reduced if technically justified. The increase or decrease in bake time **shall** be determined using the procedure in JEDEC JESD22-A120 (i.e., < 0.002 % weight loss between successive readouts) or per critical interface concentration calculations.

9. Voltage Measure Point

Voltage Measure Point		
Station	Net Name	Diode resistance
PU702	+3VSB_ATX	337
PL201	VCCGT	482
PC613	+5VSB	482
PL301	VCCIO	441
EATX12V	12V_CPU	554
PL704	VCCSA	515
TPM	+3VSB	306
D4C15	+VTTDDR	432
EATXPWR	+5VSB_ATX	592
PQ708	+5VDUAL	521
EATXPWR	+12V	487
EATXPWR	+5V	420
PQ403	+3V	315

www.aitech1.ru

10.Signal Measure Point

		Signal Measure Point	
Station	Sequence	Net Name	Diode resistance
SR120	1	S_RTCRST#	777
SR121		S_SRTCST#	777
NA	2	AC Power Switch ON	NA
PC613	3	+5VSB	482
TPM		+3VSB	306
SR80	3.1	S_DPWRCK	19
SR80	4	O_RSMRST#	19
O1R140	5	O_PWRBTN#_R	580
O1R18	6	O_IOPWRBTN#	528
O1R97	7/4.2	S_SLP_S3#	503
NA	7	S_SLP_A#	NA
NA	7.1	S_SLP_LAN#	NA
PQ532	8/4.1	S_SLP_S4#	530
O1R98	9	O_PSON#_O1	536
EATXPWR	10	12V	487
EATXPWR		5V	420
PQ403		3V	315
NA	11	B_ATX_PWROK	NA
SR1640	12	O_PWROK	36
ESDC2	13	H_CPUPWRGD	430
HR210	14	H_SIDDATA	511
PR109		H_SIDCLK	513
PC168	15	VCORE	441
SQ6	16	P_VR_READY_10	490
TPM	17	S_PLTRST#	491
ESDC3	18	H_CPURST#	391
XC75	19	O_X1_RST#	586
XC71		O_X16_RST#	587